

WHAT WE CLAIM IN THE INVENTION IS:

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- 1 1. A method of forming an interconnect structure of a semiconductor
2 device, the interconnect structure having a dielectric material deposited over an
3 underlying interconnect layer and having a via extending through the dielectric
4 material for establishing a connection between an underlying conductor and a
5 trench in an upper portion of the dielectric material, comprising the steps of:
6 (a) forming a mask layer over the dielectric material;
7 (b) forming a via in the mask layer to a first predetermined depth
8 of the mask layer;
9 (c) forming a trench in the mask layer to a second
10 predetermined depth of the mask layer, which is not as deep as said first
11 predetermined depth of the via formed in the mask layer;
12 (d) forming a via through the dielectric material to the underlying
13 conductor, corresponding to the dimensions of the via formed in the mask layer;
14 and,
15 (e) forming a trench in the dielectric material to a predetermined
16 depth of the dielectric material corresponding to the dimensions of the trench
17 formed in the mask layer.
- 1 2. The method of claim 1 further including the step of removing a
2 predetermined amount of the mask layer from the semiconductor device and
3 leaving a film of the mask layer thereon over the dielectric material.
- 1 3. The method of claim 1 wherein said dielectric material includes a
2 via dielectric layer formed over the interconnect layer, a barrier layer disposed
3 between the via dielectric layer and the interconnect layer, a trench dielectric
4 layer formed over the via dielectric layer, and an etch stop layer disposed
5 between the trench dielectric layer and the via dielectric layer.

4. The method of claim 3 wherein said step of etching the via includes etching the via through the via dielectric layer and the barrier layer, and the step of etching the trench includes etching the trench through the trench dielectric layer.

5. The method of claim 4 further including the step of removing a predetermined amount of the mask layer from the semiconductor device and leaving a film of the mask layer thereon over the dielectric material.

6. A method of forming an interconnect structure using a mask layer deposited over a dielectric material which has been deposited over an underlying interconnect layer, comprising the steps of:

(a) forming a first mask film over the dielectric material having a known set of etch properties;

(b) forming a second mask film over the first mask film having a known set of etch properties different from the etch properties of the first mask film;

(c) forming a third mask film over the second mask film having etch properties substantially identical to the etch properties of the first film; and,

(d) forming a fourth mask film over the third mask film having etch properties substantially identical to the etch properties to the etch properties of the second mask film; and

(e) selectively etching the mask films in multiple steps to form the interconnect structure.

7. The method of claim 6 further including the steps of forming a via through the dielectric material to the underlying interconnect layer and forming a trench within the dielectric material, to a predetermined depth of the dielectric material.

1 8. The method of claim 6 further including the steps of forming the via
2 in the mask layer down to the first mask film and forming the trench in the mask
3 layer down to the third mask film.

1 9. The method of claim 8 further including the steps of forming the via
2 through the dielectric material and forming the trench to a predetermined depth of
3 the dielectric material.

1 10. The method of claim 8 further including the steps of forming a via
2 through the dielectric material, forming a trench in the mask layer down to the
3 first mask layer and forming a trench in the dielectric material to a predetermined
4 depth of the dielectric material.

1 11. The method of claim 10 further including the step of removing the
2 third and fourth mask films from the semiconductor device.

1 12. The method of claim 10 further including the step of removing the
2 second mask film, the third mask film and the fourth mask film from the
3 semiconductor device.

1 13. The method of claim 8 further including the steps of forming a via
2 dielectric layer over the underlying interconnect layer, forming a trench dielectric
3 layer over the via dielectric layer, forming an etch stop layer between the via
4 dielectric layer and trench dielectric layer.

1 14. The method of claim 13 the steps of simultaneously forming the via
2 through the etch stop layer and etching the fourth mask film from the
3 semiconductor device.

1 15. The method of claim 8 further including the steps forming a barrier
2 layer between the via dielectric layer and the interconnect layer.

1 16. The method of claim 15 the steps of simultaneously forming the via
2 through the barrier layer and removing the third mask film from the
3 semiconductor device.

1 17. The method of claim 16 further including the steps of forming the
2 trench through the trench dielectric layer, and simultaneously removing the etch
3 stop layer exposed within the trench and the second mask film.

1 18. A method of forming an interconnect structure using a mask layer
2 deposited over a dielectric material which has been deposited over an underlying
3 interconnect layer, comprising the steps of:

4 (a) forming a via dielectric layer over the underlying interconnect
5 layer,

6 (b) forming a trench dielectric layer over the via dielectric layer,

7 (c) forming an etch stop layer between the via dielectric layer
8 and trench dielectric layer;

9 (d) forming a barrier layer between the via dielectric layer and
10 the interconnect layer;

11 (e) forming a first mask film over the dielectric material having a
12 known set of etch properties;

13 (f) forming a second mask film over the first mask film having a
14 known set of etch properties different from the etch properties of the first mask
15 film;

16 (g) forming a third mask film over the second mask film having
17 etch properties substantially identical to the etch properties of the first film; and

18 (h) forming a fourth mask film over the third mask film having
19 etch properties substantially identical to the etch properties to the etch properties
20 of the second mask film.

1 19. The method of claim 18 further including the steps of forming a via
2 in the mask layer down to the first mask film and forming a trench in the mask
3 layer down to the third mask film, and the trench overlapping the via.

1 22. The method of claim 21 further including the step of removing the
2 second mask film.

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